



LI DE HENG ELECTRONICS

B5817W-5819W

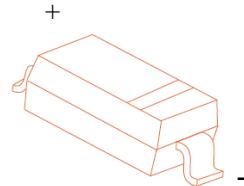
SOD-123 Plastic-Encapsulate Diode

## B5817W-5819W SCHOTTKY BARRIER DIODE

### FEATURES

For use in low voltage, high frequency inverters  
Free wheeling, and polarity protection applications.

SOD-123



### Maximum Ratings and Electrical Characteristics, Single Diode @T<sub>A</sub>=25°C

| Parameter   | Symbol   | B5817W | B5818W   | B5819W | Unit |
|---|--|--------|----------|--------|------|
| Non-Repetitive Peak reverse voltage   | V <sub>RM</sub>  | 20     | 30       | 40     | V    |
| Peak repetitive Peak reverse voltage<br>Working Peak Reverse Voltage<br>DC Blocking Voltage | V <sub>RRM</sub><br>V <sub>RWM</sub><br>V <sub>R</sub> | 20     | 30       | 40     | V    |
| RMS Reverse Voltage   | V <sub>R(RMS)</sub>                                    | 14     | 21       | 28     | V    |
| Average Rectified Output Current  | I <sub>O</sub>   |        | 1        |        | A    |
| Peak forward surge current @=8.3ms  | I <sub>FSM</sub>                                       |        | 9        |        | A    |
| Repetitive Peak Forward Current   | I <sub>FRM</sub>                                       |        | 1.5      |        | A    |
| Power Dissipation   | P <sub>d</sub>   |        | 500      |        | mW   |
| Thermal Resistance Junction to Ambient  | R <sub>θJA</sub>                                       |        | 250      |        | °C/W |
| Storage temperature   | T <sub>STG</sub>                                       |        | -65~+150 |        | °C   |

### ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)

| Parameter                       | Symbol            | Test conditions   | MIN            | MAX   | UNIT |
|---------------------------------|-------------------|---|----------------|---|------|
| Reverse breakdown voltage       | V <sub>(BR)</sub> | I <sub>R</sub> = 1mA<br>B5817W<br>B5818W<br>B5819W  | 20<br>30<br>40 |   | V    |
| Reverse voltage leakage current | I <sub>R</sub>    | V <sub>R</sub> =20V<br>V <sub>R</sub> =30V<br>V <sub>R</sub> =40V<br>B5817W<br>B5818W<br>B5819W   |                | 1   | mA   |
| Forward voltage                 | V <sub>F</sub>    | B5817W I <sub>F</sub> =1A<br>I <sub>F</sub> =3A<br>B5818W I <sub>F</sub> =1A<br>I <sub>F</sub> =3A<br>B5819W I <sub>F</sub> =1A<br>I <sub>F</sub> =3A |                | 0.45<br>0.75<br>0.55<br>0.875<br>0.6<br>0.9 | V    |
| Diode capacitance               | C <sub>D</sub>    | V <sub>R</sub> =4V, f=1MHz  |                | 120   | pF   |

**Typical Characteristics**      **B5817-5819W**  
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**1N4148WS/BAV16WS**

